IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re	App	lication	of:
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PATENT APPLICATION

Inventor:

Mark Albert Crowder

Serial No.:

Not Yet Assigned

Attorney Docket No. SLA 0629

Filed:

Herewith

Title:

2N MASK DESIGN AND METHOD OF SEQUENTIAL LATERAL SOLIDIFICATION

Hon. Commissioner for Patents Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to 37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by the Examiner and made of record in the above-identified application.

November 8, 2001 (Date)

Respectfully submitted,

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FORM PTO-1449 INFORMATION DISCLOSURE			DOCKET NUMBER 0629 APPLICATION NUMBER						
CITATION IN AN APPLICATION				APPLICANT Mark Albert Crowder					
				FILING DATE: GROUP November 8, 2001		OUP ART U	P ART UNIT CO		
		U.S. F	PATENT I	DOCUMENTS					
EXAMINER	DOCUMENT	DATE		NAME	CLASS	SUB	FIL. DATE		
INITIAL	NUMBER					CLASS	IF APPROP.		
	6,177,301	01/23/01	Jung		438	150	05/13/99		
	6,235,614	05/22/01	Yang		438	486	05/13/99		
	6,274,888	08/14/01	Suzuk	i et al.	257	72	01/10/00		
							<u> </u>		
		FOREIG	N PATEN	IT DOCUMENTS					
	DOCUMENT NUMBER	DATE		COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO		
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		OT	THER DO	CUMENTS		A			
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	Sposili et al., p	Article entitled, "Sequential Lateral Solidification of Thin Silicon Films on SiO ₂ ", by Sposili et al., published in Appl. Phys. Lett. 69 (19) 4 November 1996, pp 2864-2866							
	Manipulation a (1998), pp 603-	nd Optimizat ·617	tion", by	Lateral Growth of Si Im et al., published	in Phys. Sta	t. Sol. (a)	166, 603		
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		Article entitled, "Single-Crystal Si Films for Thin-Film Transistor Devices", by Im et al., published in Appl. Phys. Lett. 70 (25), 23 June 1997, pp 34343436							
EXAMINER				DATE CONSIDERED					